August 2000

FDC640P

P-Channel 2.5V Specified PowerTrench[™] MOSFET

General Description

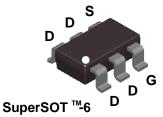
This P-Channel 2.5V specified MOSFET is produced in a rugged gate version of Fairchild Semiconductor's advanced PowerTrench process. It has been optimized for power management applications for a wide range of gate drive voltages.

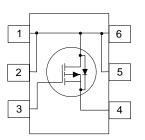
Applications

- Load switch
- Battery protection
- Power management

Features

- -4.5 A, -20 V. $R_{DS(ON)} = 0.050 \ \Omega \ @ V_{GS} = -4.5 \ V$ $R_{DS(ON)} = 0.077 \ \Omega \ @ V_{GS} = -2.5 \ V$
- Rugged gate rating (\pm 12V).
- High performance trench technology for extremely low $\rm R_{\rm DS(ON)}.$
- SuperSOT[™]-6 package: small footprint (72% smaller than standard SO-8); low profile (1mm thick).



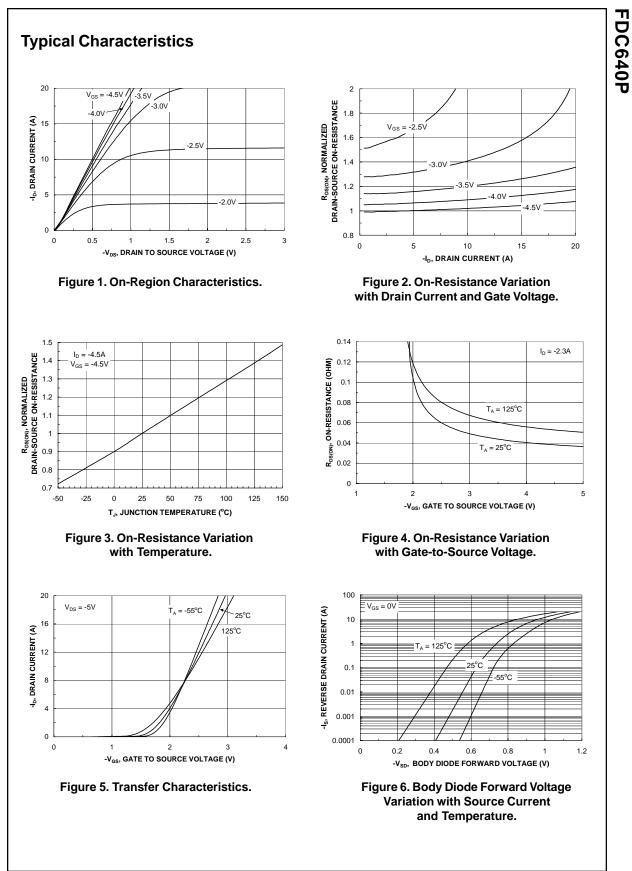


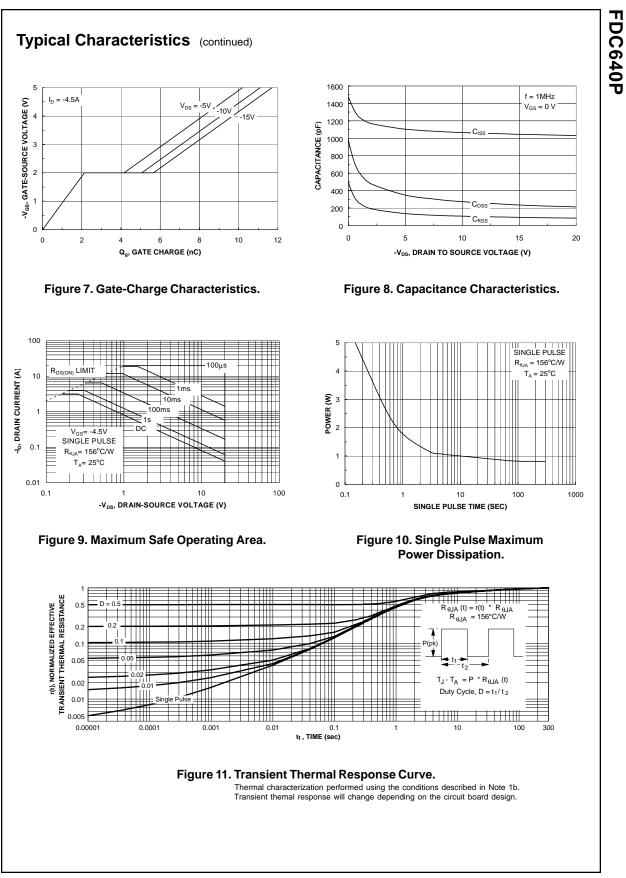
Absolute Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{DSS}	Drain-Source V	oltage		-20	V
V _{GSS}	Gate-Source Vo	oltage		<u>+</u> 12	V
I _D	Drain Current	- Continuous	(Note 1a)	-4.5	А
	Drain Current	- Pulsed		-20	
PD	Power Dissipati	on for Single Operation	(Note 1a)	1.6	W
			(Note 1b)	0.8	
T _J , T _{stq}	Operating and Storage Junction Temperature Range			-55 to +150	∘C
<mark>Therma</mark> _{R_{өл}}	I Character	istics ance, Junction-to-Ambient	t (Note 1a)	78	°C/W
R _{AJC}	Thermal Resist	ance, Junction-to-Case	(Note 1)	30	°C/W
	e Outlines a	and Ordering Inf	ormation Reel Size	Tape Width	Quantity
	640	FDC640P	7"	8mm	3000 units

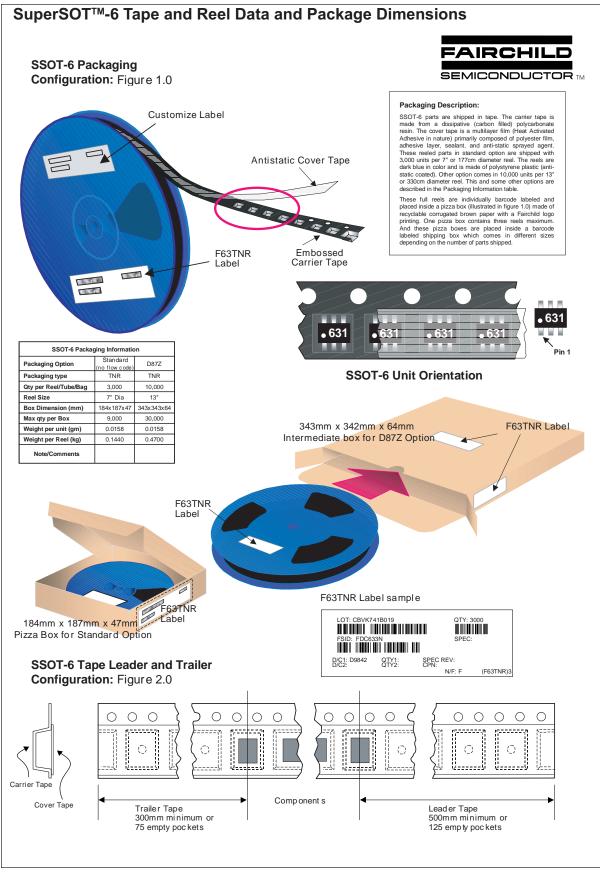
Off Char BV _{DSS}		Test Conditions	Min	Тур	Max	Units
BV _{DSS}	acteristics		-			
	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{D} = -250 \mu\text{A}$	-20			V
	Breakdown Voltage Temperature Coefficient	I_D = -250 μ A, Referenced to 25°C		-17		mV/∘C
DSS	Zero Gate Voltage Drain Current	$V_{DS} = -16 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			-1	μA
GSSF	Gate-Body Leakage Current, Forward	$V_{GS} = 12 \text{ V}, V_{DS} = 0 \text{ V}$			100	nA
GSSR	Gate-Body Leakage Current, Reverse	V_{GS} = -12 V, V_{DS} = 0 V			-100	nA
)n Chara	acteristics (Note 2)					
GS(th)	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	-0.6	-1	-1.5	V
VGS(th) $\Delta T_{,l}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250 \ \mu$ A, Referenced to 25°C		3		mV/∘C
DS(on)	Static Drain-Source $V_{GS} = -4.5 \text{ V}$, $I_D = -4.5 \text{ A}$ On-Resistance $V_{GS} = -4.5 \text{ V}$, $I_D = -4.5 \text{ A}$ $V_{GS} = -2.5 \text{ V}$, $I_D = -3.6 \text{ A}$			0.037 0.054 0.060	0.05 0.08 0.077	Ω
D(on)	On-State Drain Current	V_{GS} = -4.5 V, V_{DS} = -5 V	-10			А
FS	Forward Transconductance	$V_{DS} = -5 V, I_{D} = -4.5 A$		13		S
)vnamic	Characteristics					
viss	Input Capacitance	$V_{DS} = -25 V, V_{GS} = 0 V,$		1065		pF
oss	Output Capacitance	f = 1.0 MHz		270		pF
rss	Reverse Transfer Capacitance			105		pF
	g Characteristics (Note 2)	,				
d(on)	g Characteristics (Note 2) Turn-On Delay Time	$V_{DD} = -10 \text{ V}, \text{ I}_{D} = -1 \text{ A},$		8.5	17	ns
i(on)	Turn-On Rise Time	$V_{GS} = -4.5 \text{ V}, \text{ R}_{GEN} = 6 \Omega$		10	18	ns
l(off)	Turn-Off Delay Time	1		55	90	ns
()	Turn-Off Fall Time			25	40	ns
٥ رو	Total Gate Charge	V _{DS} = -10 V, I _D = -4.5 A,		10	14	nC
) _{gs}	Gate-Source Charge	$V_{GS} = -4.5 V,$		2.1		nC
ر ارم	Gate-Drain Charge			2.9		nC
	unas Diada Characteristica en	d Maximum Datinga				
rain-50	urce Diode Characteristics and Maximum Continuous Drain-Source Did				-1.3	А
, / _{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}, \text{ I}_{S} = -1.3 \text{ A}$ (Note 2)		-0.75	-1.2	V
otes: R _{θJA} is the of the drain pir	sum of the junction-to-case and case-to-ambient rest ns. $R_{\theta,C}$ is guaranteed by design while $R_{\theta,CA}$ is determine nen mounted on a 1.0 in ² pad of 2 oz. copper.	sistance where the case thermal reference is d	efined as			
b) 156°C/W w	hen mounted on a minimum pad.					

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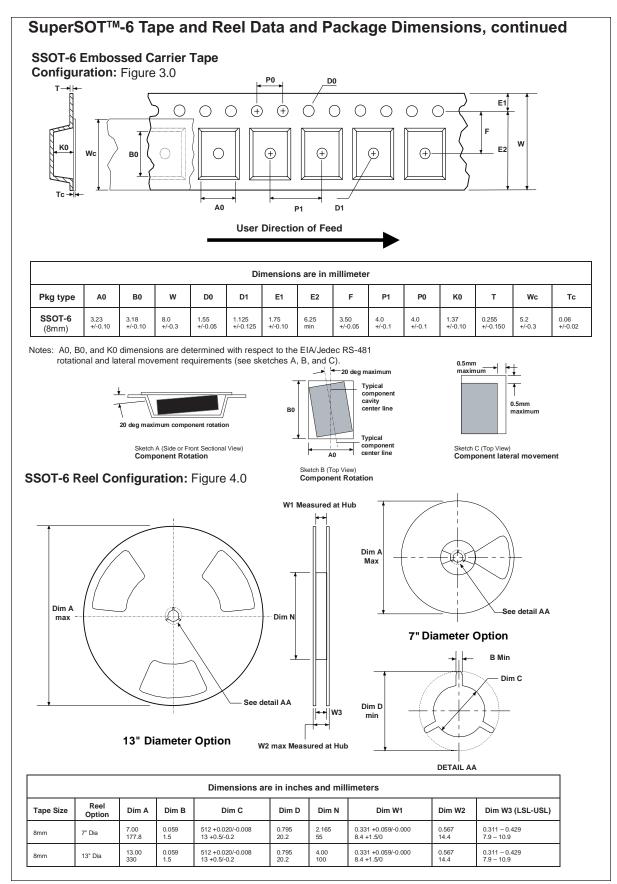




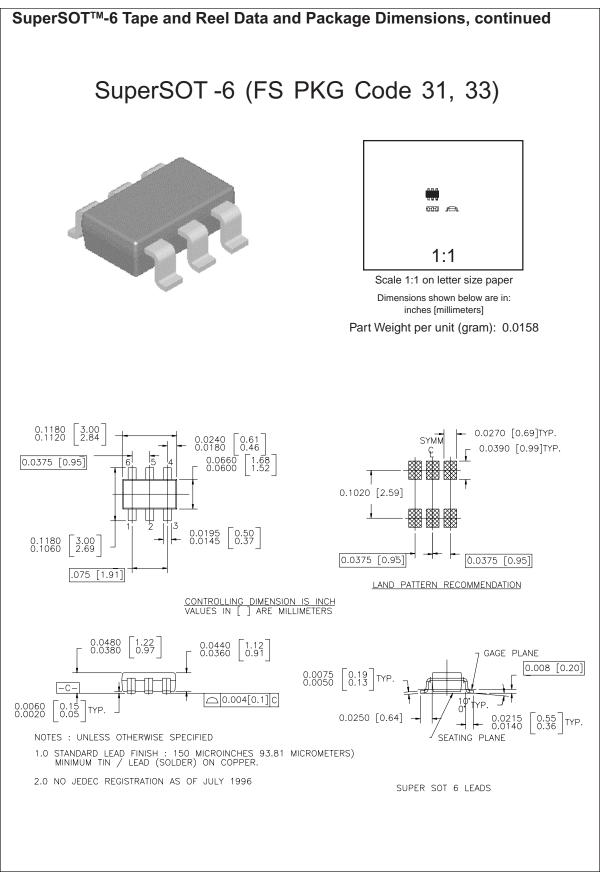
FDC640P, Rev.C



August 1999, Rev. C



July 1999, Rev. C



September 1998, Rev. A

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